

FDMA1029PZ

Dual P-Channel PowerTrench® MOSFET

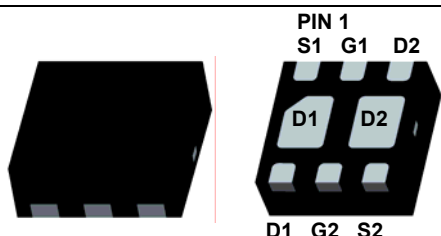
General Description

This device is designed specifically as a single package solution for the battery charge switch in cellular handset and other ultra-portable applications. It features two independent P-Channel MOSFETs with low on-state resistance for minimum conduction losses. When connected in the typical common source configuration, bi-directional current flow is possible.

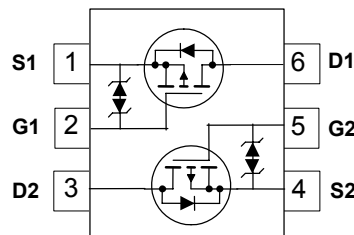
The MicroFET 2x2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.

Features

- -3.1 A, -20V. $R_{DS(ON)} = 95\text{ m}\Omega @ V_{GS} = -4.5\text{V}$
 $R_{DS(ON)} = 141\text{ m}\Omega @ V_{GS} = -2.5\text{V}$
- Low profile – 0.8 mm maximum – in the new package MicroFET 2x2 mm
- HBM ESD protection level > 2.5kV (Note 3)
- RoHS Compliant



MicroFET 2x2



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D	Drain Current – Continuous (Note 1a)	-3.1	A
	– Pulsed	-6	
P _D	Power Dissipation for Single Operation (Note 1a)	1.4	W
	(Note 1b)	0.7	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	86 (Single Operation)	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1b)	173 (Single Operation)	
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1c)	69 (Dual Operation)	
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1d)	151 (Dual Operation)	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
029	FDMA1029PZ	7"	8mm	3000 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		-12		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate–Body Leakage	$V_{GS} = \pm 12\text{ V}, V_{DS} = 0\text{ V}$			± 10	μA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.6	-1.0	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		4		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}, I_D = -3.1\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -2.5\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -3.1\text{ A}, T_J = 125^\circ\text{C}$		60 88 87	95 141 140	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -3.1\text{ A}$		-11		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		540		pF
C_{oss}	Output Capacitance			120		pF
C_{rss}	Reverse Transfer Capacitance			100		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		13	24	ns
t_r	Turn–On Rise Time			11	20	ns
$t_{d(off)}$	Turn–Off Delay Time			37	59	ns
t_f	Turn–Off Fall Time			36	58	ns
Q_g	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -3.1\text{ A},$ $V_{GS} = -4.5\text{ V}$		7.0	10	nC
Q_{gs}	Gate–Source Charge			1.1		nC
Q_{gd}	Gate–Drain Charge			2.4		nC

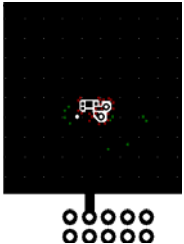
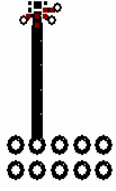
Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				–1.1	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = -1.1\text{ A}$ (Note 2)		–0.8	–1.2	V
t_{rr}	Diode Reverse Recovery Time	$I_F = -3.1\text{ A}$, $di_F/dt = 100\text{ A}/\mu\text{s}$		25		ns
Q_{rr}	Diode Reverse Recovery Charge			9		nC

Notes:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.
 - $R_{\theta JA} = 86^\circ\text{C/W}$ when mounted on a 1in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB
 - $R_{\theta JA} = 173^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper
 - $R_{\theta JA} = 69^\circ\text{C/W}$ when mounted on a 1in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB
 - $R_{\theta JA} = 151^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper

	<p>a) 86°C/W when mounted on a 1in² pad of 2 oz copper</p>		<p>b) 173°C/W when mounted on a minimum pad of 2 oz copper</p>
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Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

3. The diode connected between the gate and source serves only protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics

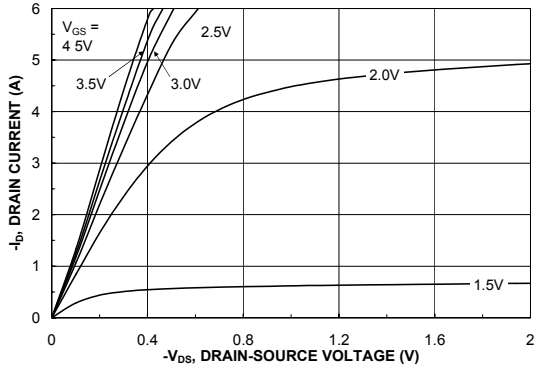


Figure 1. On-Region Characteristics.

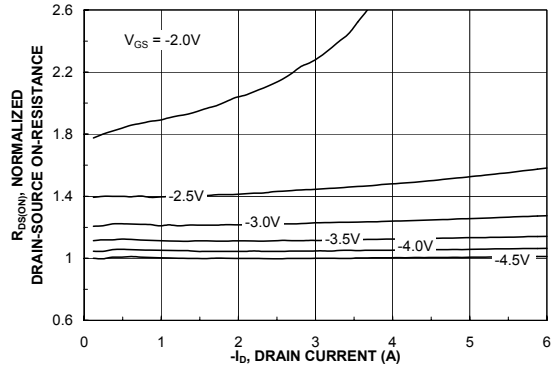


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

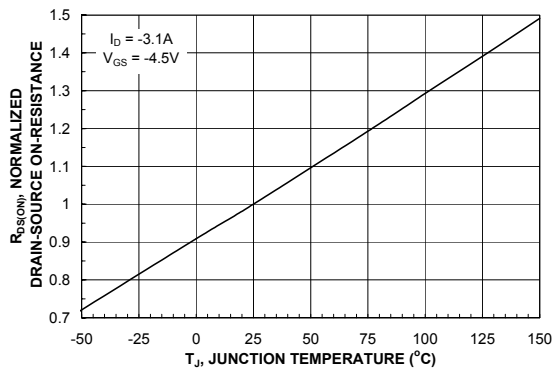


Figure 3. On-Resistance Variation with Temperature.

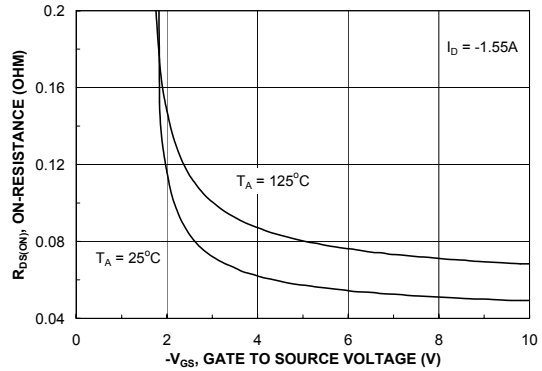


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

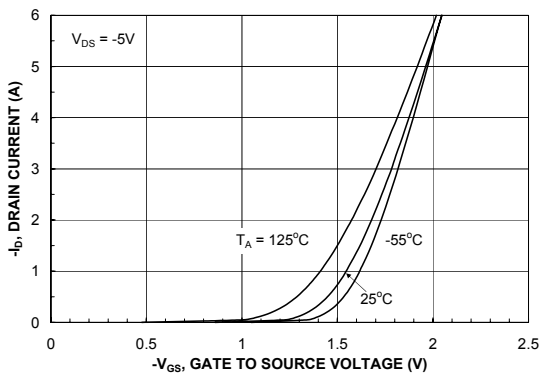


Figure 5. Transfer Characteristics.

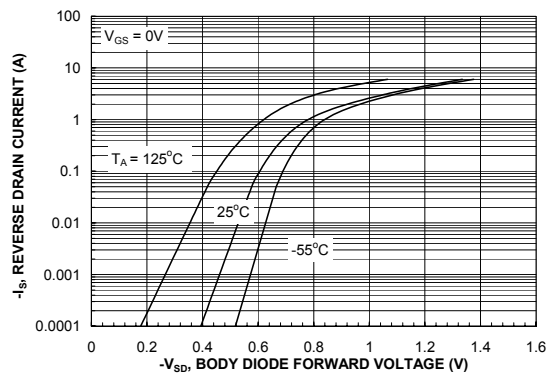


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

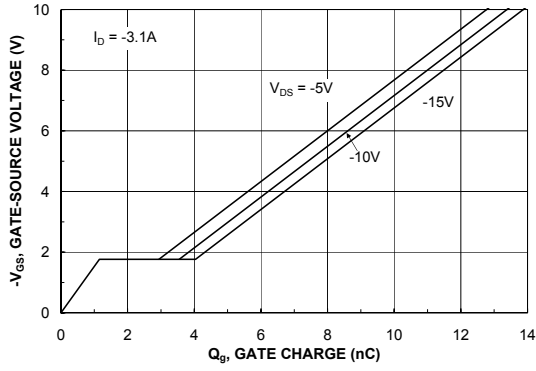


Figure 7. Gate Charge Characteristics.

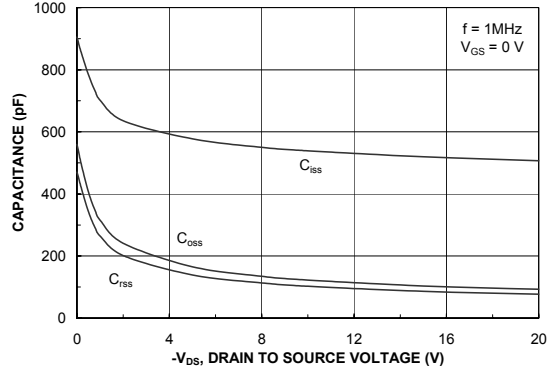


Figure 8. Capacitance Characteristics.

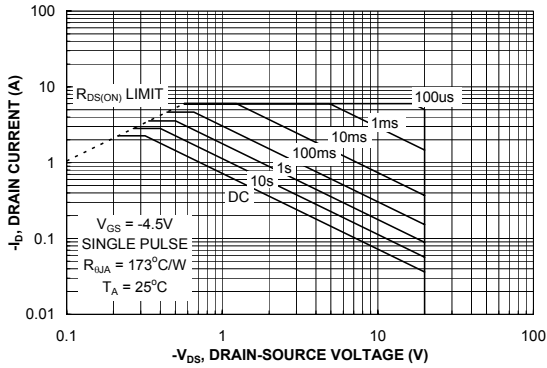


Figure 9. Maximum Safe Operating Area.

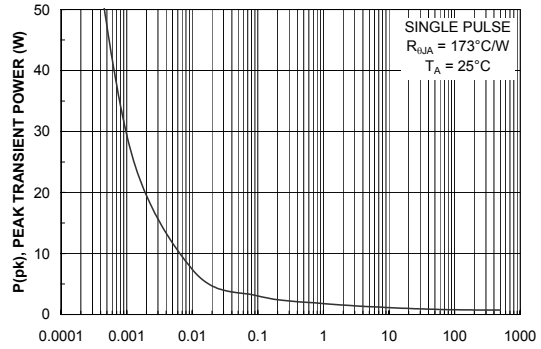


Figure 10. Single Pulse Maximum Power Dissipation.

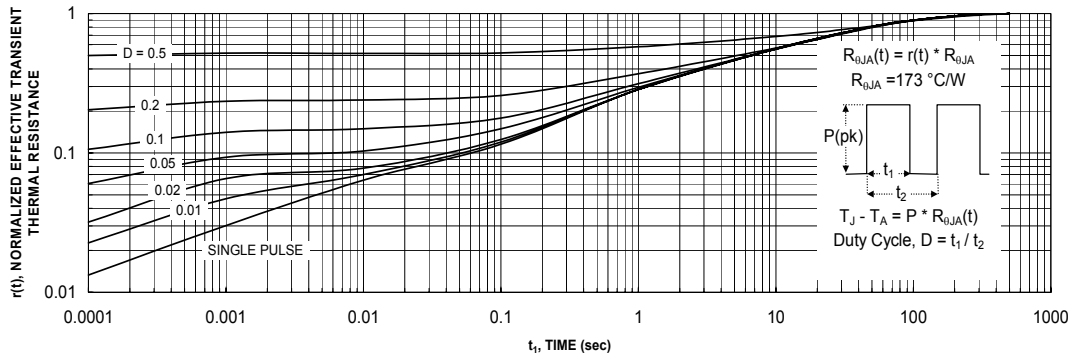
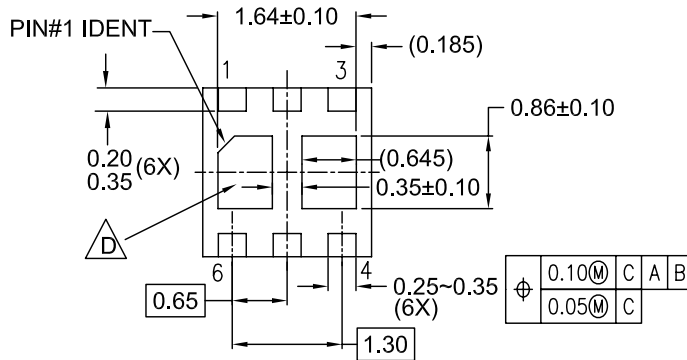
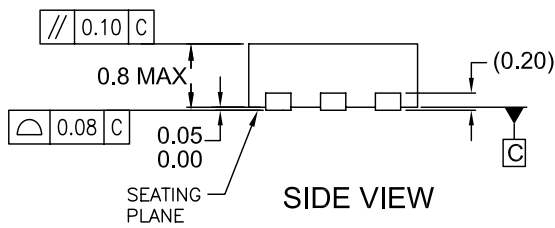
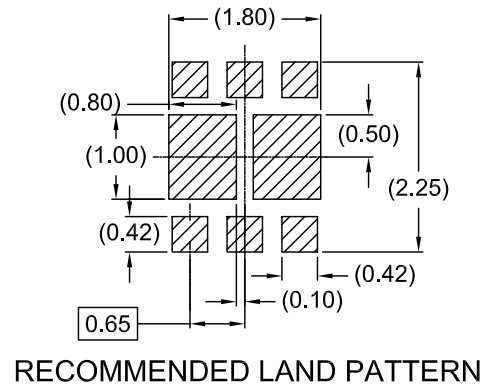
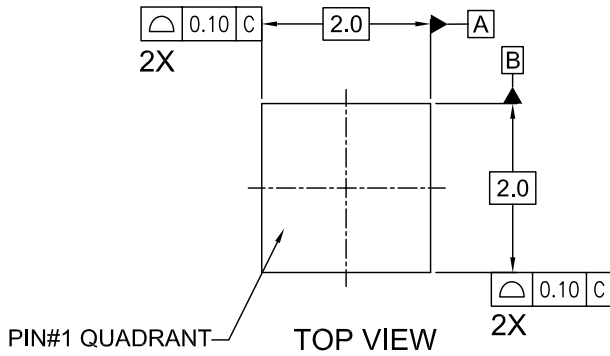


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

Dimensional Outline and Pad Layout



NOTES:

A. CONFORMS TO JEDEC REGISTRATION MO-229, VARIATION VCCC EXCEPT AS NOTED.

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994





 NON-JEDEC DUAL DAP

E. DRAWING FILE NAME : MLP06J rev3



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